

N-channel 600 V, 0.150  $\Omega$ , 19.5 A, FDmesh™ II Power MOSFET  
(with fast diode) D<sup>2</sup>PAK, I<sup>2</sup>PAK, TO-220, TO-220FP, TO-247

## Features

Type	$V_{DSS}$ (@ $T_{jmax}$ )	$R_{DS(on)}$ max.	$I_D$
STx23NM60ND	650 V	< 0.180 $\Omega$	19.5 A

- The worldwide best  $R_{DS(on)}$ \* area amongst the fast recovery diode devices
- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance
- High dv/dt and avalanche capabilities

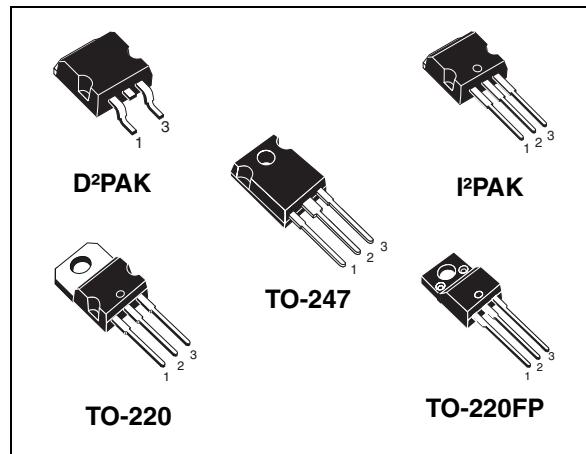


Figure 1. Internal schematic diagram

AM01475v1

## Application

Switching applications

## Description

The device is an N-channel FDmesh™ II Power MOSFET that belongs to the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a new vertical structure to the company's strip layout and associates all advantages of reduced on-resistance and fast switching with a n intrinsic fast-recovery body diode. It is therefore strongly recommended for bridge topologies, in particular ZVS phase-shift converters.

Table 1. Device summary

Part number	Marking	Package	Packaging
STB23NM60ND	23NM60ND	D <sup>2</sup> PAK	Tape and reel
STI23NM60ND	23NM60ND	I <sup>2</sup> PAK	Tube
STF23NM60ND	23NM60ND	TO-220FP	Tube
STP23NM60ND	23NM60ND	TO-220	Tube
STW23NM60ND	23NM60ND	TO-247	Tube

## Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value		Unit
		D <sup>2</sup> PAK, I <sup>2</sup> PAK TO-220, TO-247	TO-220FP	
V <sub>DS</sub>	Drain-source voltage (V <sub>GS</sub> =0)	600		V
V <sub>GS</sub>	Gate-source voltage	± 25		V
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25 °C	19.5	19.5 <sup>(1)</sup>	A
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 100 °C	11.7	11.7 <sup>(1)</sup>	A
I <sub>DM</sub> <sup>(2)</sup>	Drain current (pulsed)	78	78 <sup>(1)</sup>	A
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25 °C	150	35	W
dv/dt <sup>(3)</sup>	Peak diode recovery voltage slope	40		V/ns
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; T <sub>C</sub> = 25 °C)		2500	V
T <sub>stg</sub>	Storage temperature	-55 to 150		°C
T <sub>j</sub>	Max. operating junction temperature	150		°C

1. Limited only by maximum temperature allowed
2. Pulse width limited by safe operating area
3. I<sub>SD</sub> ≤ 19.5 A, di/dt ≤ 600 A/μs, V<sub>DD</sub> = 80% V<sub>(BR)DSS</sub>

**Table 3. Thermal data**

Symbol	Parameter	D <sup>2</sup> PAK	I <sup>2</sup> PAK	TO-220	TO-247	TO-220FP	Unit
R <sub>thj-case</sub>	Thermal resistance junction-case max		0.83			3.6	°C/W
R <sub>thj-amb</sub>	Thermal resistance junction-amb max		62.5	50	62.5		°C/W
T <sub>I</sub>	Maximum lead temperature for soldering purposes		300				°C

**Table 4. Avalanche characteristics**

Symbol	Parameter	Max value	Unit
I <sub>AS</sub>	Avalanche current, repetitive or not-repetitive (pulse width limited by T <sub>j</sub> max)	9	A
E <sub>AS</sub>	Single pulse avalanche energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AS</sub> , V <sub>DD</sub> = 50 V)	700	mJ

## 2 Electrical characteristics

( $T_{CASE} = 25^\circ\text{C}$  unless otherwise specified)

**Table 5. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1 \text{ mA}, V_{GS} = 0$	600			V
$dv/dt^{(1)}$	Drain-source voltage slope	$V_{DD} = 480 \text{ V}, I_D = 19.5 \text{ A}, V_{GS} = 10 \text{ V}$		30		V/ns
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max rating}, V_{DS} = \text{Max rating, } @ 125^\circ\text{C}$			1 100	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20 \text{ V}$			100	nA
$V_{GS(\text{th})}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	3	4	5	V
$R_{DS(\text{on})}$	Static drain-source on resistance	$V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$		0.150	0.180	$\Omega$

1. Characteristic value at turn off on inductive load

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15 \text{ V}, I_D = 10 \text{ A}$	-	17	-	S
$C_{iss}$ $C_{oss}$ $C_{rss}$	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 50 \text{ V}, f = 1 \text{ MHz}, V_{GS} = 0$	-	2050 80 8	-	pF pF pF
$C_{oss \text{ eq.}}^{(2)}$	Equivalent output capacitance	$V_{GS} = 0, V_{DS} = 0 \text{ to } 480 \text{ V}$	-	318	-	pF
$R_g$	Gate input resistance	f=1 MHz Gate DC Bias=0 Test signal level=20 mV open drain	-	4	-	$\Omega$
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 480 \text{ V}, I_D = 19.5 \text{ A}$ $V_{GS} = 10 \text{ V}$ (see Figure 19)	-	70 10 30	-	nC nC nC

1. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

2.  $C_{oss \text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

**Table 7. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300 \text{ V}, I_D = 10 \text{ A}, R_G = 4.7 \Omega, V_{GS} = 10 \text{ V}$ (see Figure 18)	-	25	-	ns
$t_r$	Rise time			45	-	ns
$t_{d(off)}$	Turn-off delay time			90	-	ns
$t_f$	Fall time			40	-	ns

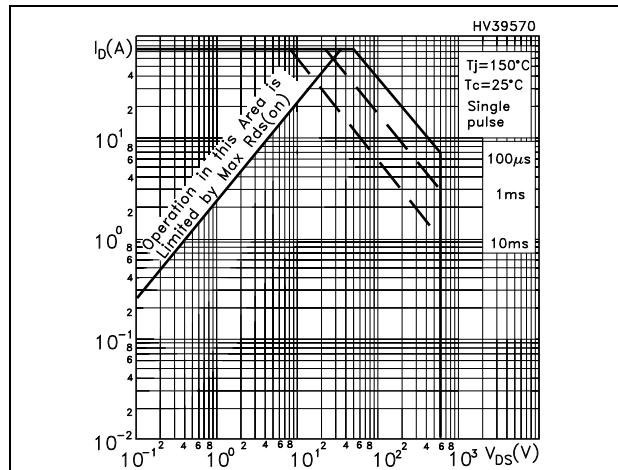
**Table 8. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-	19.5	78	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)					
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 19.5 \text{ A}, V_{GS}=0$	-	-	1.3	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 19.5 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}, V_{DD} = 100 \text{ V}$ (see Figure 20)	-	190	-	ns
$Q_{rr}$	Reverse recovery charge			1.2	-	$\mu\text{C}$
$I_{RRM}$	Reverse recovery current			13	-	A
$t_{rr}$	Reverse recovery time	$V_{DD} = 100 \text{ V}$ $di/dt = 100 \text{ A}/\mu\text{s}, I_{SD} = 19.5 \text{ A}$ $T_j = 150^\circ\text{C}$ (see Figure 20)	-	260	-	ns
$Q_{rr}$	Reverse recovery charge			2.0	-	$\mu\text{C}$
$I_{RRM}$	Reverse recovery current			15	-	A

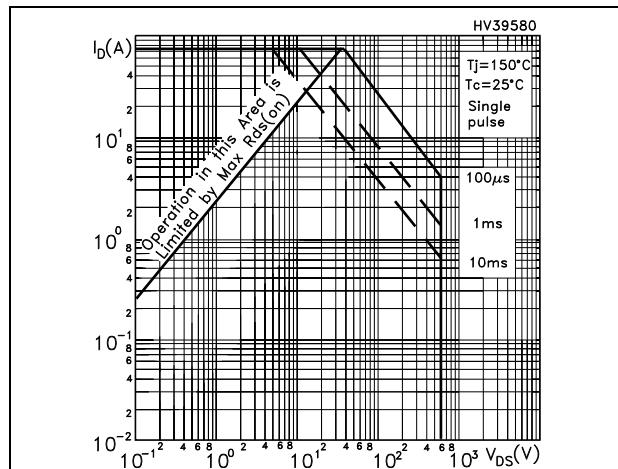
1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

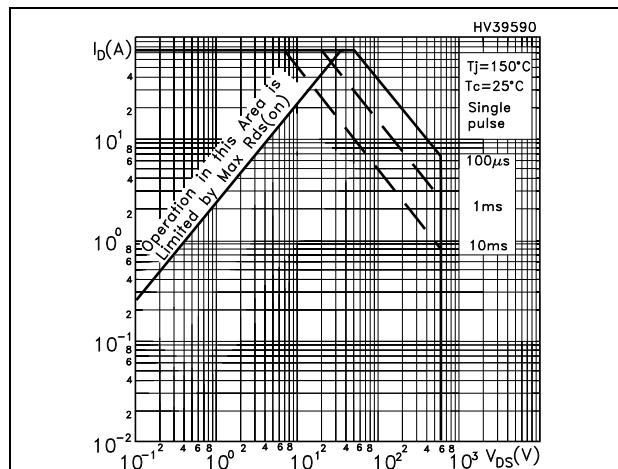
**Figure 2.** Safe operating area for TO-220, D<sup>2</sup>PAK, I<sup>2</sup>PAK



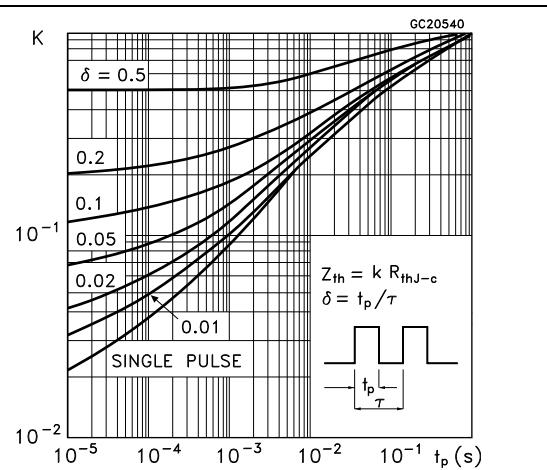
**Figure 4.** Safe operating area for TO-220FP



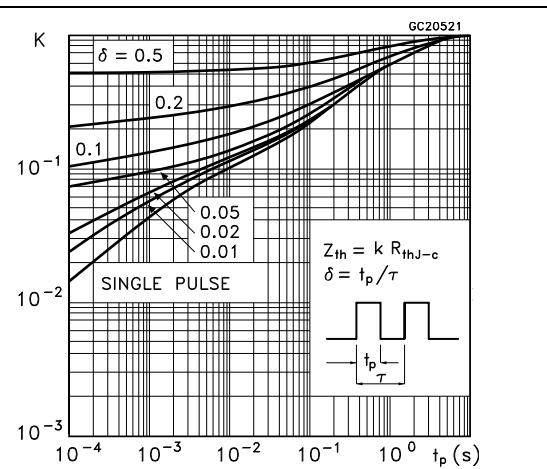
**Figure 6.** Safe operating area for TO-247



**Figure 3.** Thermal impedance for TO-220, D<sup>2</sup>PAK, I<sup>2</sup>PAK



**Figure 5.** Thermal impedance for TO-220FP



**Figure 7.** Thermal impedance for TO-247

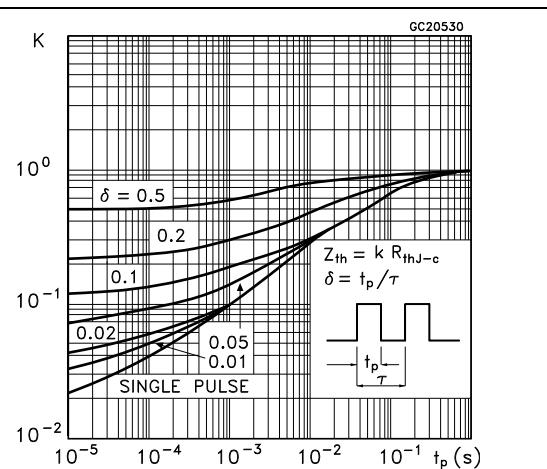


Figure 8. Output characteristics

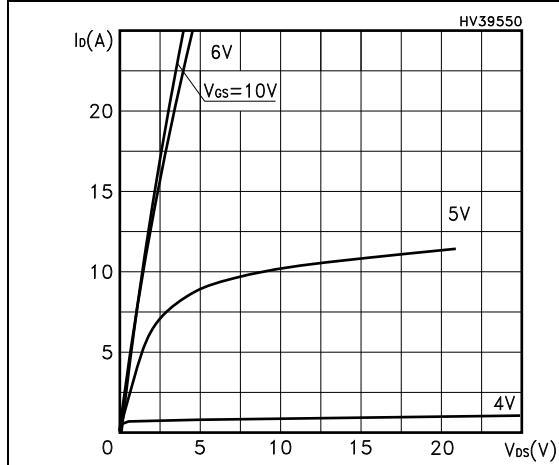


Figure 9. Transfer characteristics

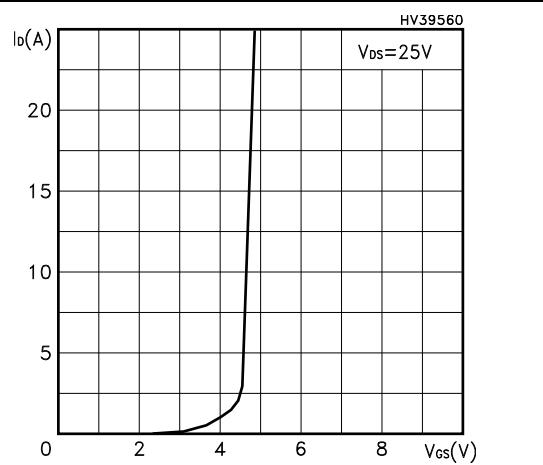


Figure 10. Transconductance

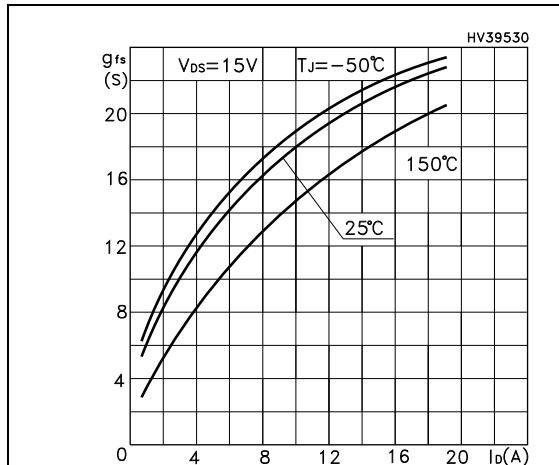


Figure 11. Static drain-source on resistance

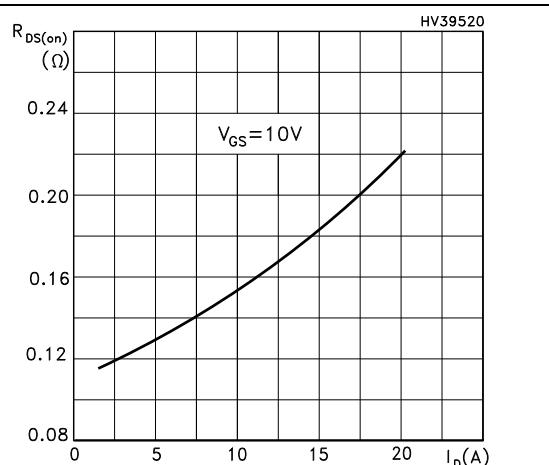
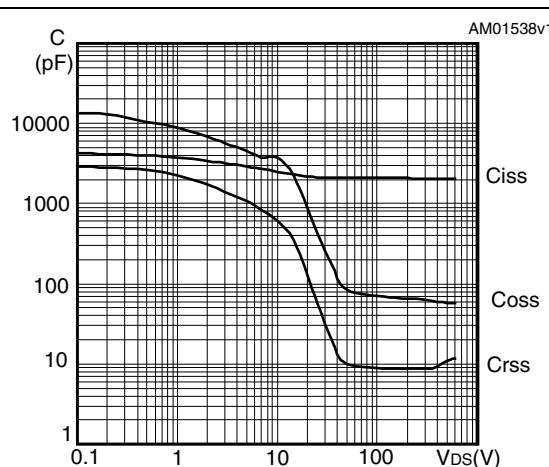
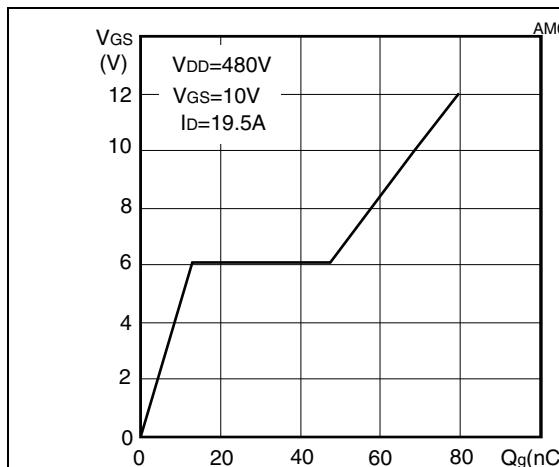
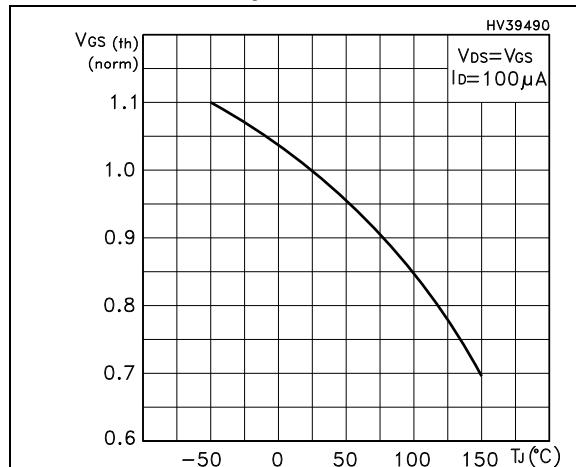
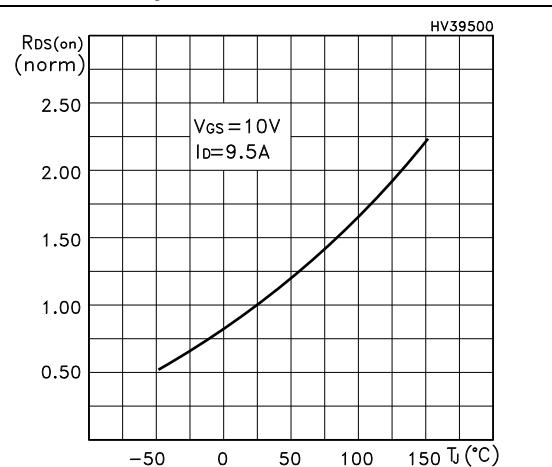
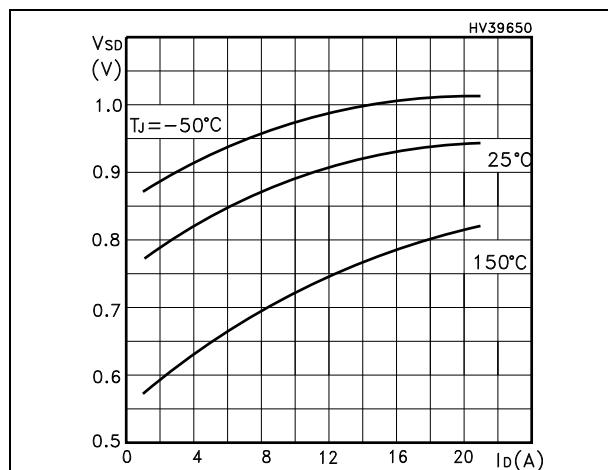
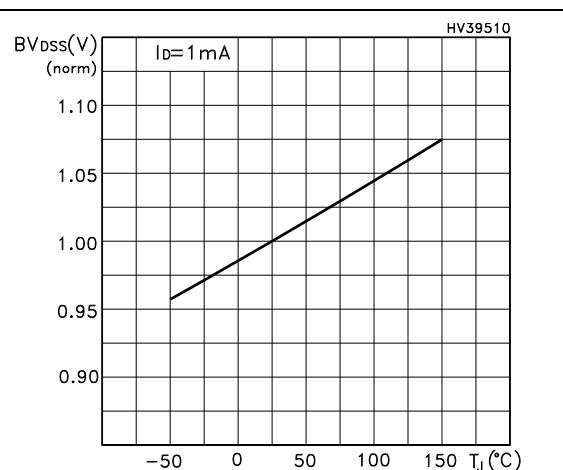


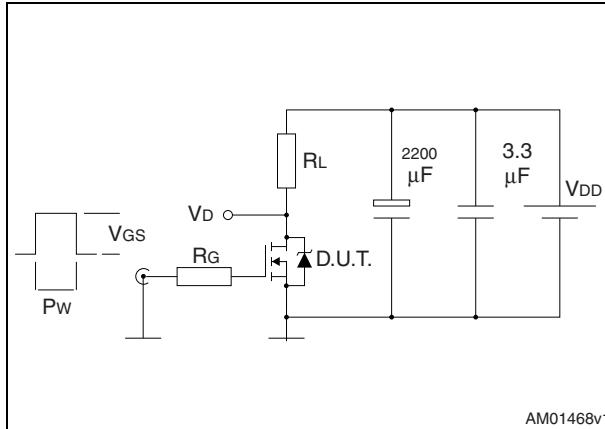
Figure 12. Gate charge vs gate-source voltage



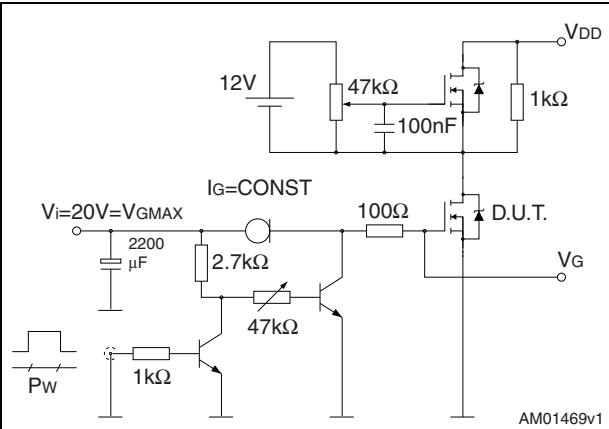
**Figure 14. Normalized gate threshold voltage vs temperature****Figure 15. Normalized on resistance vs temperature****Figure 16. Source-drain diode forward characteristics****Figure 17. Normalized BV<sub>DSS</sub> vs temperature**

### 3 Test circuits

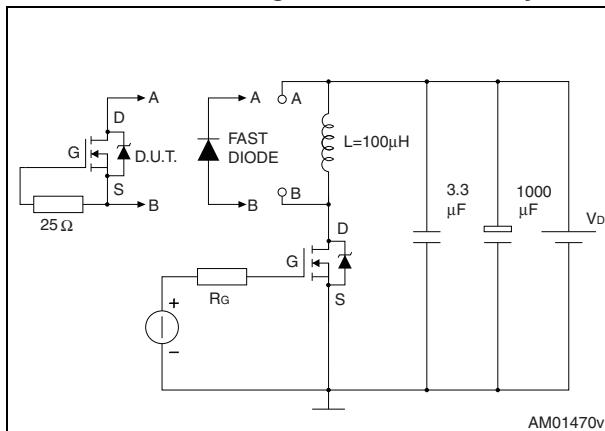
**Figure 18. Switching times test circuit for resistive load**



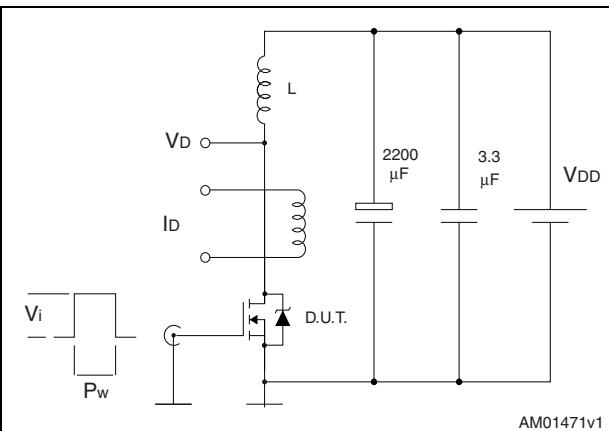
**Figure 19. Gate charge test circuit**



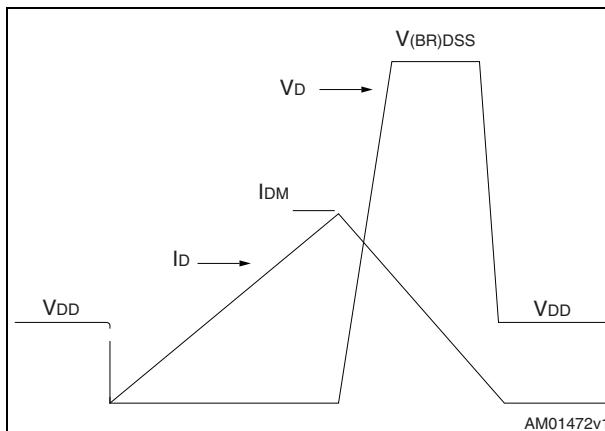
**Figure 20. Test circuit for inductive load switching and diode recovery times**



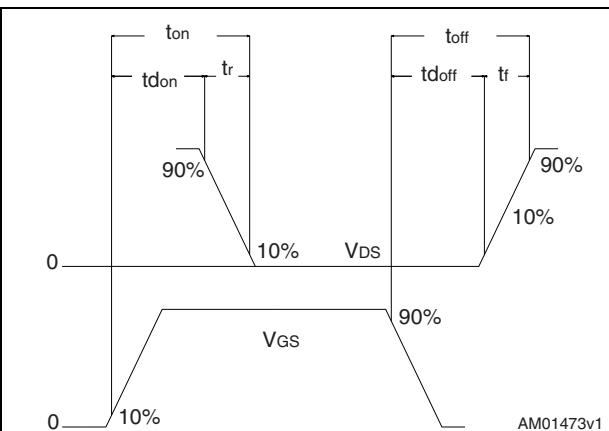
**Figure 21. Unclamped inductive load test circuit**



**Figure 22. Unclamped inductive waveform**



**Figure 23. Switching time waveform**

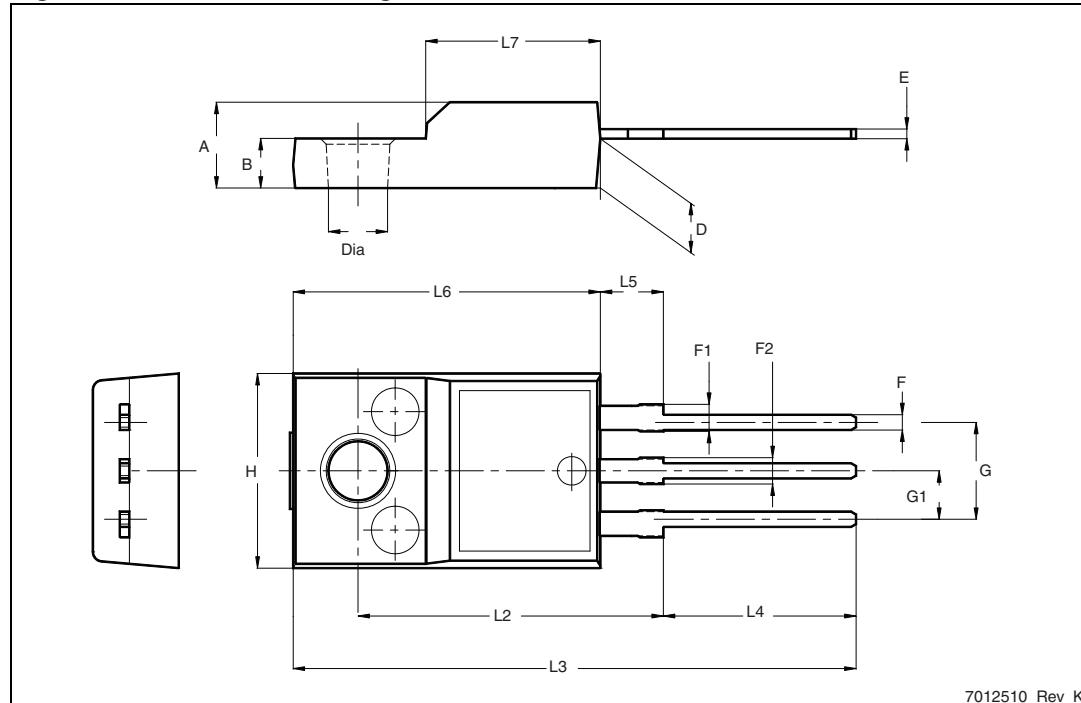


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com).  
ECOPACK® is an ST trademark.

**Table 9.** TO-220FP mechanical data

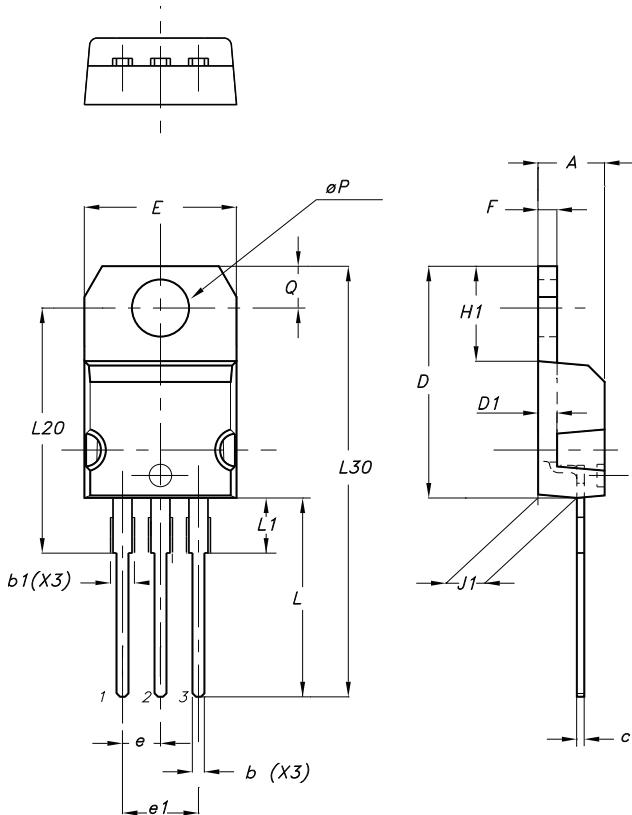
Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

**Figure 24.** TO-220FP drawing

7012510\_Rev\_K

## TO-220 type A mechanical data

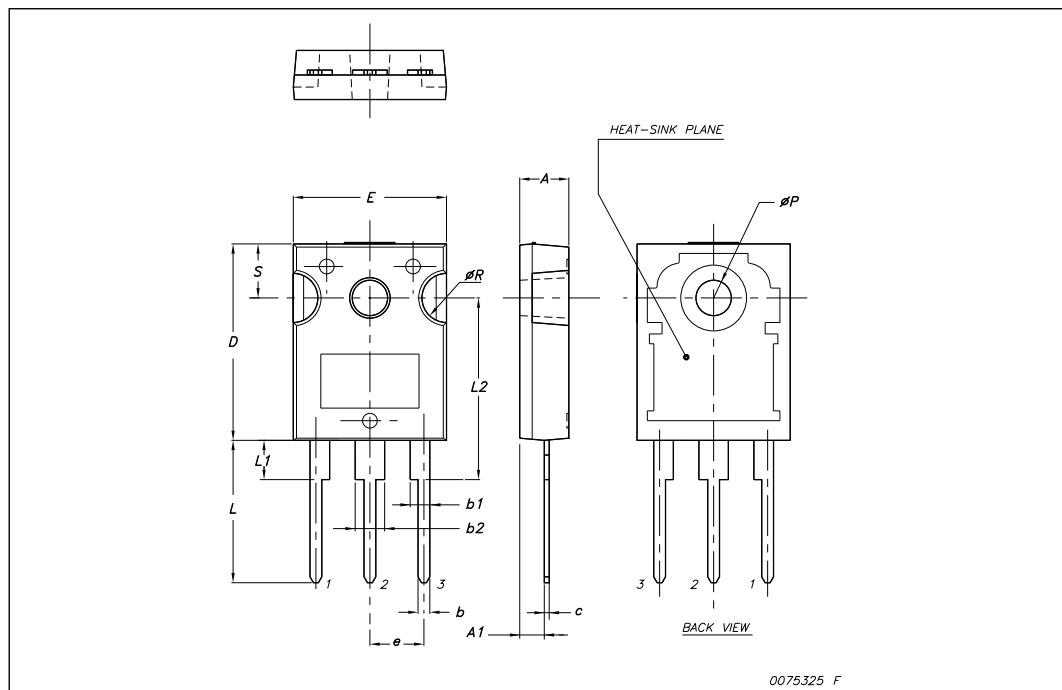
Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
$\emptyset P$	3.75		3.85
Q	2.65		2.95



0015988\_Rev\_S

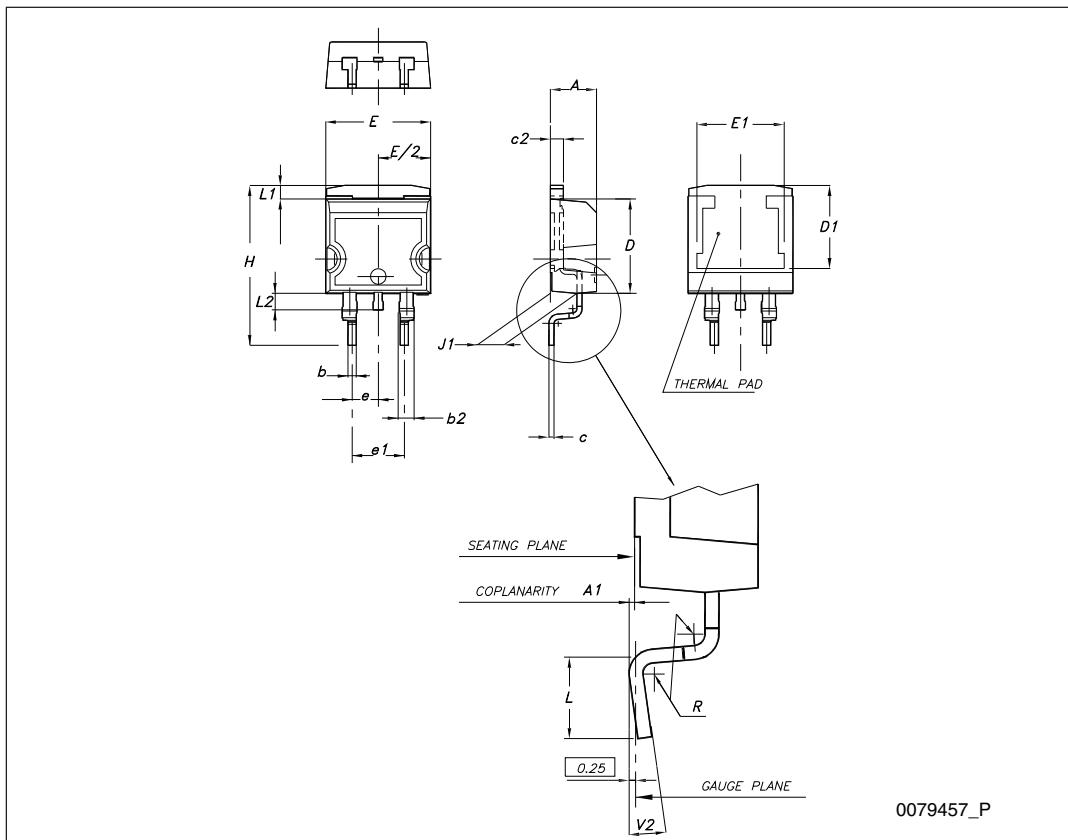
## TO-247 Mechanical data

Dim.	mm.		
	Min.	Typ	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
øP	3.55		3.65
øR	4.50		5.50
S		5.50	



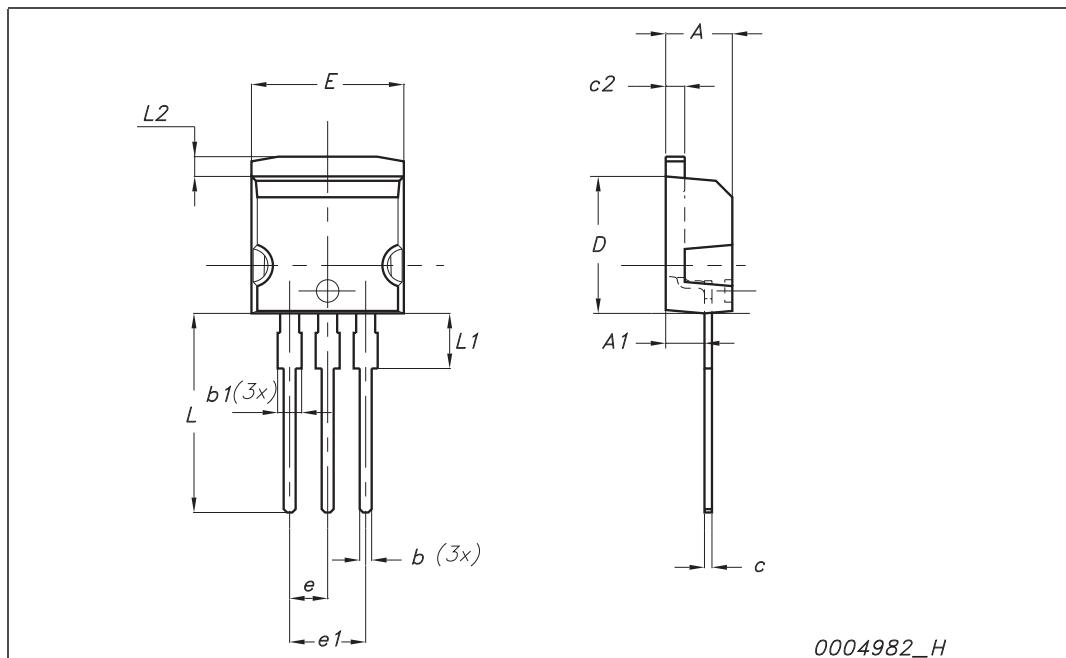
D<sup>2</sup>PAK (TO-263) mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

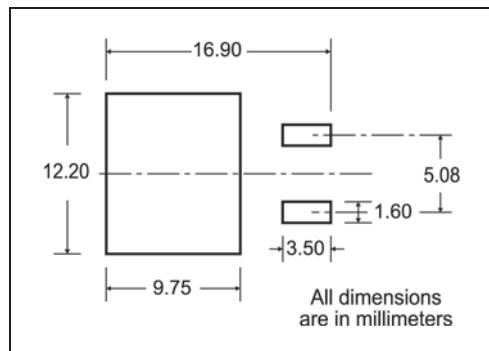


I<sup>2</sup>PAK (TO-262) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



## 5 Packaging mechanical data

D<sup>2</sup>PAK FOOTPRINT

TAPE AND REEL SHIPMENT

REEL MECHANICAL DATA				
DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197
BASE QTY		BULK QTY		
1000		1000		

**TAPE MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A <sub>0</sub>	10.5	10.7	0.413	0.421
B <sub>0</sub>	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D <sub>1</sub>	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K <sub>0</sub>	4.8	5.0	0.189	0.197
P <sub>0</sub>	3.9	4.1	0.153	0.161
P <sub>1</sub>	11.9	12.1	0.468	0.476
P <sub>2</sub>	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

## 6 Revision history

**Table 10. Document revision history**

Date	Revision	Changes
22-Jan-2008	1	First release
11-Dec-2008	2	Document status promoted from preliminary data to datasheet.
06-Oct-2010	3	Corrected unit in <a href="#">Table 5: On/off states</a>

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